

REMARKS

Claims 1-25 remain in this application.

Entry of the above amendments is earnestly solicited.

An early and favorable first action on the merits is earnestly requested.

Should there be any matters that need to be resolved in the present application, the Examiner is respectfully requested to contact the undersigned at the telephone number listed below.

The Commissioner is hereby authorized in this, concurrent, and future replies, to charge payment or credit any overpayment to Deposit Account No. 25-0120 for any additional fees required under 37 C.F.R. § 1.16 or under 37 C.F.R. § 1.17.

Respectfully submitted,

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APPENDIX:

The Appendix includes the following item(s):

- a new or amended Abstract of the Disclosure

ABSTRACT OF THE DISCLOSURE

Nonvolatile semiconductor memory devices and methods for manufacturing thereof, which provide inhibiting the shortcircuiting of the channel due to the creation of the bird's beak to promote the manufacturing of the devices with higher-density or higher-integration, lowering the operation voltage and improving the characteristics of maintaining the electric charge, without complicating the manufacturing process. Immediately after forming ONO films comprising a first silicon oxide film, a second silicon nitride film and a third silicon oxide film on a silicon substrate, a silicon layer is formed, and then, arsenic ions are implanted over the silicon layer and/or ONO films to form a bit line, and a second electrical conductive layer is deposited while remaining the silicon layer to form a word line comprising a dual layer structure of two electrical conductive layers.